

BYC10X-600P Hyperfast power diode Rev.01 - 3 September 2018

Product data sheet

1. General description

Hyperfast power diode in a SOD113A (2-lead TO-220-F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- · High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Values			Unit	
Absolute	e maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V	
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _h ≤ 61 °C; Fig. 1; Fig. 2	10		A		
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _h ≤ 61 °C; square-wave pulse	20		A		
I _{FSM}	non-repetitive peak forward current	$t_{\rm p}$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 4</u>		150			А
		t_{p} = 8.3 ms; $T_{j(\text{init})}$ = 25 °C; sine-wave pulse	165		А		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 4</u>		-	2.5	3.2	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 4</u>		-	1.3	2	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$		-	12	18	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 5}$		-	19	-	ns

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	
2	А	anode		К — К — А
mb	n.c.	mounting base; isolated		001aaa020

6. Ordering information

Table 3. Ordering information							
Type number	Package	ge					
	Name	Description	Version				
BYC10X-600P TO-220F		plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113A				

7. Marking

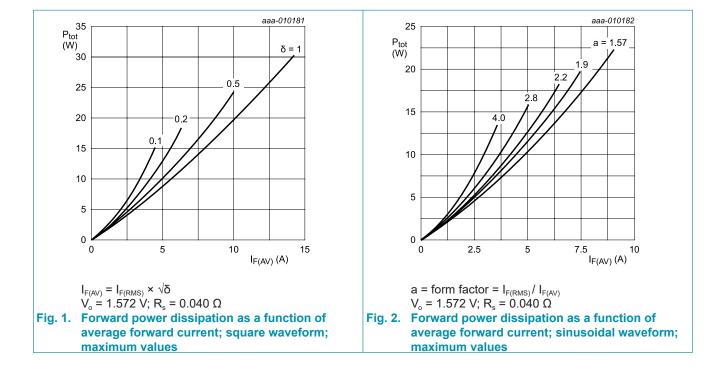
Table 4. Marking codes						
	Type number	Marking codes				
	BYC10X-600P	BYC10X-600P				

8. Limiting values

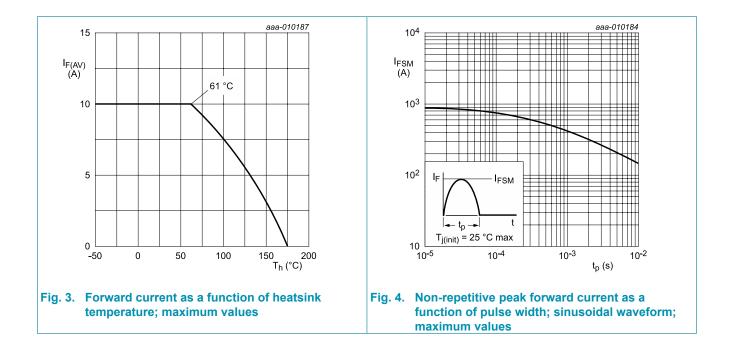
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V _R	reverse voltage	DC	600	V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _h ≤ 61 °C; Fig. 1; Fig. 2; Fig. 3	10	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _h ≤ 61 °C; square-wave pulse	20	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	150	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	165	A
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C

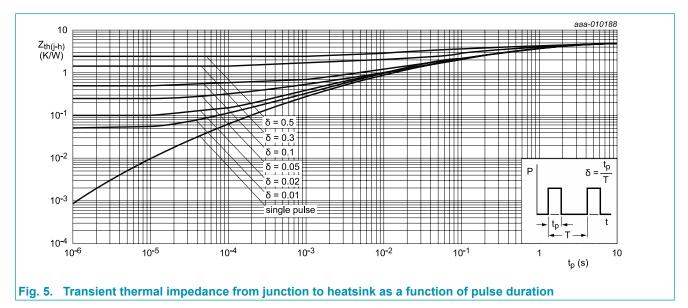


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9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig 5	-	-	4.8	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



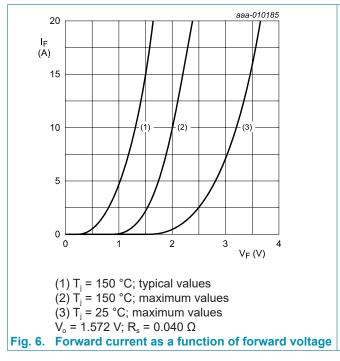
10. Isolation characteristics

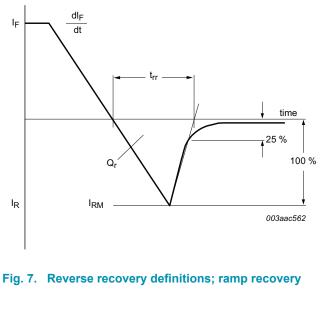
Table 7. Isolation characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz		-	10	-	PF

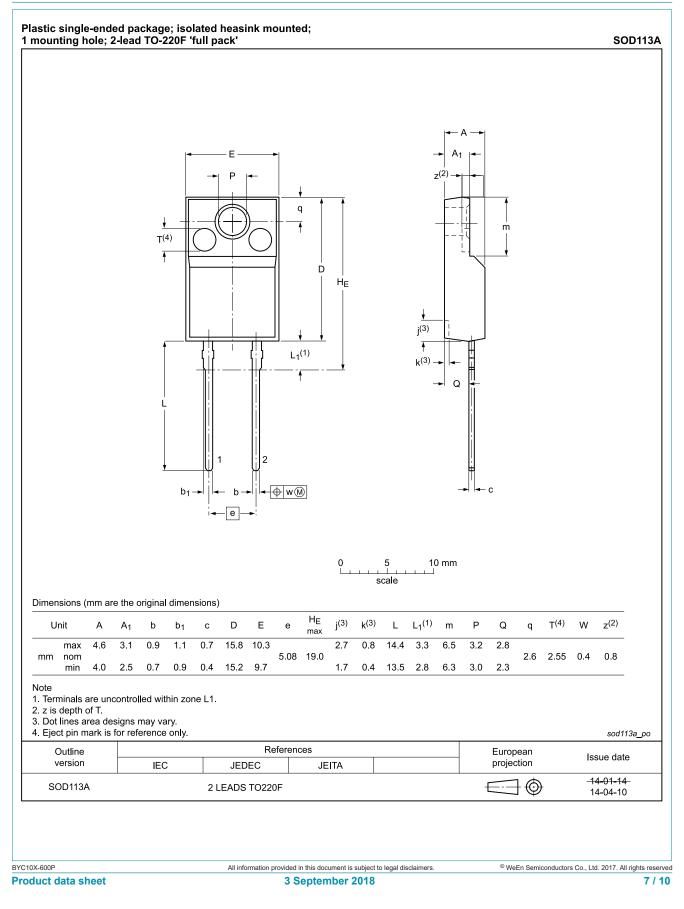
11. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics	· · · ·				
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.5	3.2	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.3	2	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	0.8	mA
Dynamic	characteristics	· · · ·				
Q _r	recovered charge	I _F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	26	-	nC
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; $T_j = 125 \text{ °C}; Fig. 7$	-	83	-	nC
t _{rr} reverse	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	12	18	ns
		$I_{F} = 10 \text{ A}; V_{R} = 400 \text{ V}; \text{ d}I_{F}/\text{d}t = 500 \text{ A}/\mu\text{s}; T_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 7}$	-	19	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	26	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	34	-	
I _{RM}	peak reverse recovery current	$I_{F} = 10 \text{ A}; V_{R} = 200 \text{ V}; \text{ d}I_{F}/\text{d}t = 200 \text{ A}/\mu\text{s}; T_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 7}$	-	2	-	A
		I _F = 10 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _i = 125 °C; <u>Fig. 7</u>	-	4.8	-	А





12. Package outline



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Hyperfast power diode

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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